54F/74F657 Octal Bidirectional Transceiver with 8-Bit Parity Generator/Checker and TRI-STATE® Outputs

General Description

The 'F657 contains eight non-inverting buffers with TRI-STATE® outputs and an 8-bit parity generator/checker. It is intended for bus-oriented applications. The buffers have a guaranteed current sinking capability of 24 mA (20 mA mil) at the A port and 64 mA (48 mA mil) at the B port.

Features

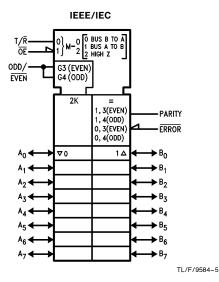
- 300 Mil 24-pin slimline DIP
- Combines 'F245 and 'F280A functions in one package
- TRI-STATE outputs
- B Outputs sink 64 mA (48 mA mil)
- 12 mA source current, B side
- Input diodes for termination effects

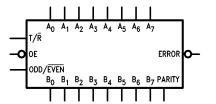
Commercial	Military	Package Number	Package Description		
74F657SPC		N24C	24-Lead (0.300" Wide) Molded Dual-In-Line		
	54F657SDM (Note 2)	J24F	24-Lead (0.300" Wide) Ceramic Dual-In-Line		
75F657SC (Note 1)		M24B	24-Lead (0.300" Wide) Molded Small Outline, JEDEC		
	54F657FM (Note 2)	W24C	24-Lead Cerpack		
	54F657LM (Note 2)	E28A	24-Lead Ceramic Leadless Chip Carrier, Type C		

Note 1: Devices also available in 13" reel. Use suffix = SCX.

Note 2: Military grade device with environmental and burn-in processing. Use suffix = DMQB, FMQB and LMQB.

Logic Symbols

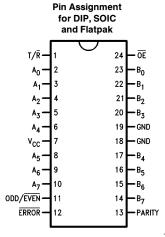


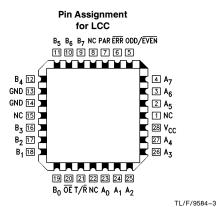


TL/F/9584-1

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Connection Diagrams





TL/F/9584-2

Unit Loading/Fan Out

		54F/74F					
Pin Names	Description	U.L. HIGH/LOW	Input I _{IH} /I _{IL} Output I _{OH} /I _{OL}				
A ₀ -A ₇	Data Inputs/	4.5/0.15	90 μΑ/ – 90 μΑ				
	TRI-STATE Outputs	150/40 (33.3)	-3 mA/24 mA (20 mA)				
B ₀ -B ₇	Data Inputs/	3.5/0.117	70 μΑ/ – 70 μΑ				
	TRI-STATE Outputs	600/106.6 (80)	-12 mA/64 mA (48 mA)				
T/R	Transmit/Receive Input	2.0/0.067	40 μΑ/ – 40 μΑ				
ŌĒ	Enable Input	2.0/0.067	40 μΑ/ – 40 μΑ				
PARITY	Parity Input/	3.5/0.117	70 μΑ/ – 70μΑ				
	TRI-STATE Output	600/106.6 (80)	-12 mA/64 mA (48 mA)				
ODD/EVEN	ODD/EVEN Parity Input	1.0/0.033	20 μΑ/ – 20 μΑ				
ERROR	Error Output	600/106.6 (80)	-12 mA/64 mA (48 mA)				

Functional Description

The Transmit/Receive (T/\overline{R}) input determines the direction of the data flow through the bidirectional transceivers. Transmit (active HIGH) enables data from the A port to the B port; Receive (active LOW) enables data from the B port to the A port.

The Output Enable (\overline{OE}) input disables the parity and \overline{ERROR} outputs and both the A and B ports by placing them in a HIGH-Z condition when the Output Enable input is HIGH.

When transmitting (T/ \overline{R} HIGH), the parity generator detects whether an even or odd number of bits on the A port are HIGH and compares these with the condition of the pari-

ty select (ODD/EVEN). If the Parity Select is HIGH and an even number of A inputs are HIGH, the Parity output is HIGH

In receiving mode (T/ \overline{R} LOW), the parity select and number of HIGH inputs on port B are compared to the condition of the Parity input. If an even number of bits on the B port are HIGH, the parity select is HIGH, and the PARITY input is HIGH, then \overline{ERROR} will be HIGH to indicate no error. If an odd number of bits on the B port are HIGH, the parity select is HIGH, and the PARITY input is HIGH, the \overline{ERROR} will be LOW indicating an error.

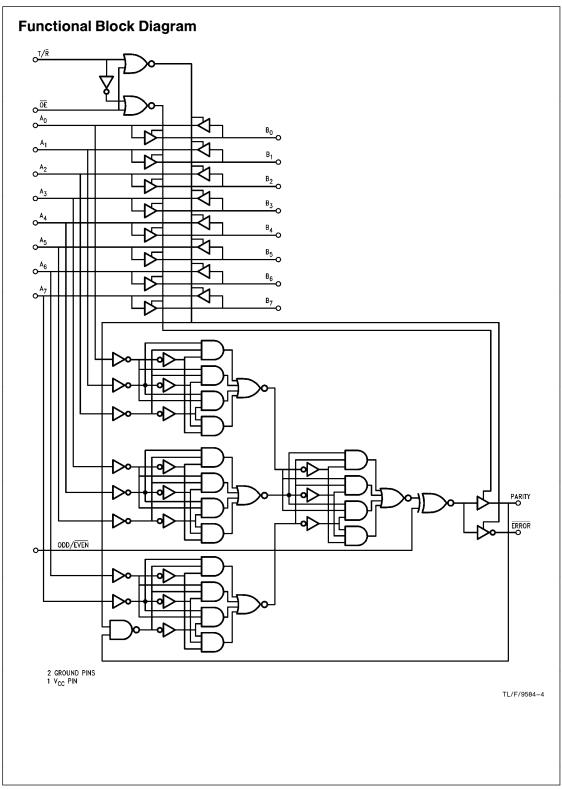
Function Table										
Number of Inputs That		Input	s	Input/ Output	Outputs					
Are High	OE T∕R ODD/EVEN			Parity	ERROR Outputs Mo					
0, 2, 4, 6, 8	L	Н	Н	Н	Z	Transmit				
	L	Н	L	L	Z	Transmit				
	L	L	Н	Н	Н	Receive				
	L	L	Н	L	L	Receive				
	L	L	L	Н	L	Receive				
	L	L	L	L	Н	Receive				
1, 3, 5, 7	L	Н	Н	L	Z	Transmit				
	L	Н	L	Н	Z	Transmit				
	L	L	Н	Н	L	Receive				
	L	L	Н	L	Н	Receive				
	L	L	L	Н	Н	Receive				
	L	L	L	L	L	Receive				

H = HIGH Voltage Level
L = LOW Voltage Level
X = Immaterial
Z = High Impedance

Function Table

Inp	outs	Outputs
ŌĒ	T/R	Outputs
L	L	Bus B Data to Bus A
L	Н	Bus A Data to Bus B
Н	X	High-Z State

 $[\]begin{split} \mathsf{H} &= \mathsf{HIGH} \; \mathsf{Voltage} \; \mathsf{Level} \\ \mathsf{L} &= \mathsf{LOW} \; \mathsf{Voltage} \; \mathsf{Level} \\ \mathsf{X} &= \mathsf{Immaterial} \end{split}$



Absolute Maximum Ratings (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

 $\begin{array}{lll} \mbox{Storage Temperature} & -65^{\circ}\mbox{C to} + 150^{\circ}\mbox{C} \\ \mbox{Ambient Temperature under Bias} & -55^{\circ}\mbox{C to} + 125^{\circ}\mbox{C} \\ \mbox{Junction Temperature under Bias} & -55^{\circ}\mbox{C to} + 175^{\circ}\mbox{C} \\ \mbox{Plastic} & -55^{\circ}\mbox{C to} + 150^{\circ}\mbox{C} \\ \end{array}$

V_{CC} Pin Potential to

Ground Pin -0.5V to +7.0V Input Voltage (Note 2) -0.5V to +7.0V

Input Current (Note 2) -30 mA to +5.0 mA

Voltage Applied to Output

in HIGH State (with $V_{CC} = 0V$)

 $\begin{array}{lll} \text{Standard Output} & -0.5 \text{V to V}_{\text{CC}} \\ \text{TRI-STATE Output} & -0.5 \text{V to } +5.5 \text{V} \end{array}$

Current Applied to Output

in LOW State (Max) twice the rated I_{OL} (mA)

Note 1: Absolute maximum ratings are values beyond which the device may be damaged or have its useful life impaired. Functional operation under these conditions is not implied.

Note 2: Either voltage limit or current limit is sufficient to protect inputs.

Recommended Operating Conditions

Free Air Ambient Temperature

Supply Voltage

Military +4.5V to +5.5V Commercial +4.5V to +5.5V

DC Electrical Characteristics

Symbol	Parameter	54F/74F			Units	v _{cc}	Conditions	
Symbol	raidilietei	Min	Тур	Max	Units	▼CC	Conditions	
V _{IH}	Input HIGH Voltage	2.0			٧		Recognized as a HIGH Signal	
V _{IL}	Input LOW Voltage			0.8	٧		Recognized as a LOW Signal	
V _{CD}	Input Clamp Diode Voltage			-1.2	٧	Min	$I_{\text{IN}} = -18 \text{mA}$	
V _{OH}	Output HIGH 54F 10% V _{CC} Voltage 54F 10% V _{CC} 54F 10% V _{CC} 74F 10% V _{CC} 74F 10% V _{CC} 74F 10% V _{CC} 74F 5% V _{CC} 74F 5% V _{CC}	2.5 2.4 2.0 2.5 2.4 2.0 2.7 2.7			V	Min	$\begin{split} I_{OH} &= -1 \text{ mA } (A_n) \\ I_{OH} &= -3 \text{ mA } (A_n, B_n, Parity, \overline{ERROR}) \\ I_{OH} &= -12 \text{ mA } (B_n, Parity, \overline{ERROR}) \\ I_{OH} &= -1 \text{ mA } (A_n) \\ I_{OH} &= -3 \text{ mA } (A_n B_n, Parity, \overline{ERROR}) \\ I_{OH} &= -15 \text{ mA } (B_n, Parity, \overline{ERROR}) \\ I_{OH} &= -1 \text{ mA } (A_n) \\ I_{OH} &= -3 \text{ mA } (A_n, B_n, Parity, \overline{ERROR}) \end{split}$	
V _{OL}	Output LOW 54F 10% V _{CC} Voltage 54F 10% V _{CC} 74F 10% V _{CC} 74F 10% V _{CC}			0.5 0.55 0.5 0.55	٧	Min	$\begin{array}{l} I_{OL} = 20 \text{ mA } (A_n) \\ I_{OL} = 48 \text{ mA } (B_n, \text{Parity, } \overline{\text{ERROR}}) \\ I_{OL} = 24 \text{ mA } (A_n) \\ I_{OL} = 64 \text{ mA } (B_n \text{ Parity, } \overline{\text{ERROR}}) \end{array}$	
I _{IH}	Input HIGH Current			20 40	μΑ	Max	$V_{IN} = 2.7V (ODD/\overline{EVEN})$ $V_{IN} 2.7V (T/\overline{R}, \overline{OE})$	
I _{BVI}	Input HIGH Current Breakdown Test			100	μΑ	V _{CC} = 0	$V_{IN} = 7.0V (T/\overline{R}, \overline{OE}, ODD/\overline{EVEN})$	
I _{BVIT}	Input HIGH Current Breakdown Test (I/O)			1.0 2.0	mA	Max	$V_{IN} = 5.5V$ (Parity, B _n) $V_{IN} = 5.5V$ (A _n)	
I _{IL}	Input LOW Current			-20 -40	μΑ	Max	$V_{IN} = 0.5V \text{ (ODD/}\overline{\text{EVEN}}\text{)}$ $V_{IN} = 0.5V \text{ (T/}\overline{\text{R}}, \overline{\text{OE}}\text{)}$	
lozh	Output Leakage Current			50	μΑ	Max	V _{OUT} = 2.7V (ERROR)	
I _{OZL}	Output Leakage Current			-50	μΑ	Max	V _{OUT} = 0.5V (ERROR)	
I _{IH} + I _{OZH}	Output Leakage Current			70 90	μΑ	Max	$V_{I/O} = 2.7V (B_n, Parity)$ $V_{I/O} = 2.7V (A_n)$	
I _{IL} + I _{OZL}	Output Leakage Current			-70 -90	μΑ	Max	$V_{I/O} = 0.5V (B_n, Parity)$ $V_{I/O} = 0.5V (A_n)$	
los	Output Short-Circuit Current	-60 -100		-150 -225	mA	Max	$V_{OUT} = 0V (A_n)$ $V_{OUT} = 0V (B_n, Parity, \overline{ERROR})$	
I _{CEX}	Output HIGH Leakage Current			250 1.0 2.0	μA mA mA	Max Max Max	$ \begin{array}{l} V_{OUT} = V_{CC} (\overline{ERROR}) \\ V_{OUT} = V_{CC} (B_n, Parity) \\ V_{OUT} = V_{CC} (A_n) \end{array} $	
I _{ZZ}	Bus Drainage Test			500	μΑ	0.0V	$V_{OUT} = 5.25V (A_n, B_n, Parity, \overline{ERROR})$	
Icch	Power Supply Current		101	125	mA	Max	V _O = HIGH	
ICCL	Power Supply Current		112	150	mA	Max	$V_O = LOW$	
I _{CCZ}	Power Supply Current		109	145	mA	Max	V _O = HIGH Z	

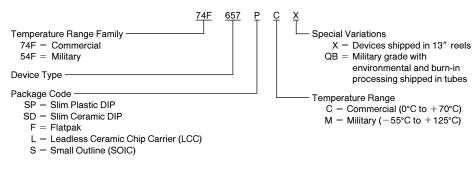
AC Electrical Characteristics

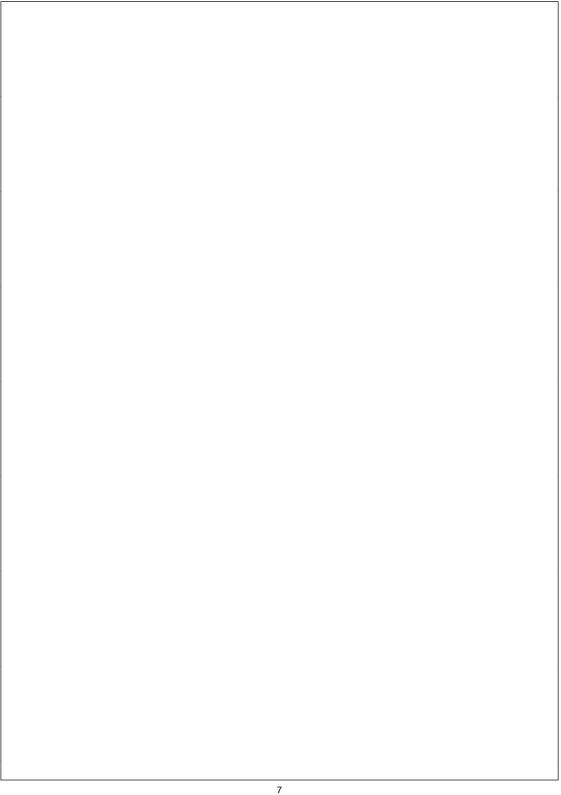
		$74F$ $T_{A} = +25^{\circ}C$ $V_{CC} = +5.0V$ $C_{L} = 50 pF$			5	4F	74F		
Symbol	Parameter				T _A , V _{CC} = Mil C _L = 50 pF		T _A , V _{CC} = Com C _L = 50 pF		Units
		Min	Тур	Max	Min	Max	Min	Max	
t _{PLH} t _{PHL}	Propagation Delay A _n to B _n , B _n to A _n	2.5 3.0	4.5 49	8.0 7.5	2.5 3.0	9.5 8.5	2.5 3.0	9.0 8.0	ns
t _{PLH} t _{PHL}	Propagation Delay An to Parity	6.5 7.0	10.1 10.9	14.0 15.0	5.5 5.5	18.0 20.5	6.0 6.0	16.0 16.5	ns
t _{PLH} t _{PHL}	Propagation Delay ODD/EVEN to PARITY	4.5 4.5	7.8 8.8	11.0 12.0	4.0 4.5	14.0 16.5	4.0 4.5	13.0 13.5	ns
t _{PLH} t _{PHL}	Propagation Delay ODD/EVEN to ERROR	4.5 4.5	7.5 8.2	11.0 12.0	4.0 4.5	14.0 16.5	4.0 4.5	13.0 13.5	ns
t _{PLH} t _{PHL}	Propagation Delay B _n to ERROR	8.0 8.0	14.0 15.0	20.5 21.5	7.5 7.5	27.0 28.5	7.5 7.5	23.0 23.5	ns
t _{PLH}	Propagation Delay PARITY to ERROR	7.0 7.5	10.8 11.8	15.5 16.5	6.0 6.5	20.0 22.0	6.0 7.5	17.0 18.5	ns
t _{PZH} t _{PZL}	Output Enable Time OE to A _n /B _n	3.0 4.0	5.0 6.5	8.0 10.0	2.5 3.5	11.0 13.5	2.5 3.5	9.5 11.0	ns
t _{PHZ}	Output Disable Time OE to A _n /B _n	1.0 1.0	4.5 4.9	8.0 7.5	1.0 1.0	9.5 8.5	1.0 1.0	9.0 8.0	ns
t _{PZH} t _{PZL}	Output Enable Time OE to ERROR (Note 1)	3.0 4.0	5.0 7.7	8.0 10.0	2.5 3.5	11.0 13.5	2.5 3.5	9.5 11.0	ns
t _{PHZ}	Output Disable Time OE to ERROR	1.0 1.0	4.5 4.9	8.0 7.5	1.0 1.0	9.5 8.5	1.0 1.0	9.0 8.0	ns
t _{PZH} t _{PZL}	Output Enable Time OE to PARITY	3.0 4.0	5.0 7.7	8.0 10.0	2.5 3.5	11.0 13.5	2.5 3.5	9.5 11.0	ns
t _{PHZ}	Output Disable Time OE to PARITY	1.0 1.0	4.6 5.1	8.0 7.5	1.0 1.0	9.5 8.5	1.0 1.0	9.0 8.0	ns

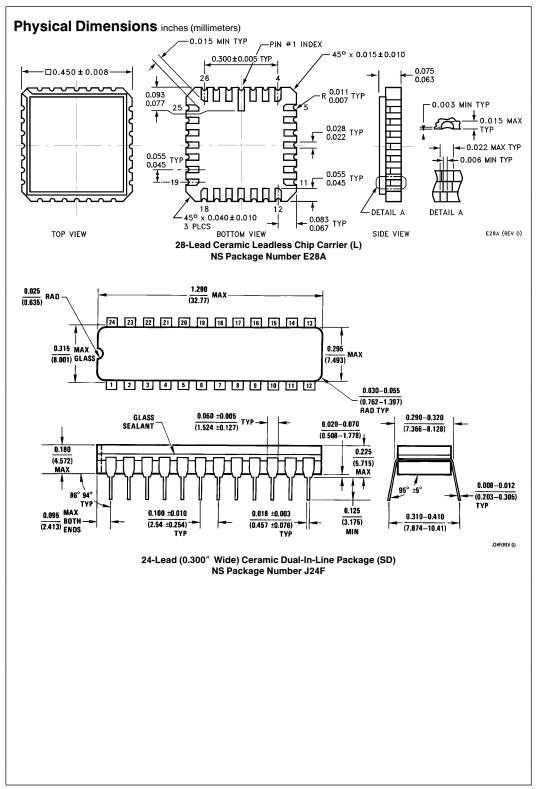
Note 1: These delay times reflect the TRI-STATE recovery time only and not the signal time through the buffers or the parity check circuity. To assure VALID information at the ERROR pin, time must be allowed for the signal to propagate through the drivers (B to A), through the parity check circuitry (same as A to PARITY), and to the ERROR output after the ERROR pin has been enabled (Output Enable times). VALID data at the ERROR pin \geq (A to PARITY) + (Output Enable Time).

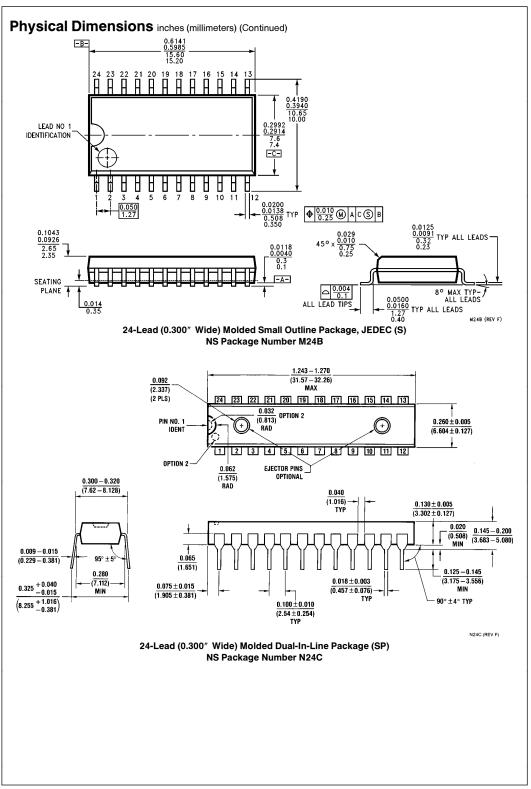
Ordering Information

The device number is used to form part of a simplified purchasing code where a package type and temperature range are defined as follows:

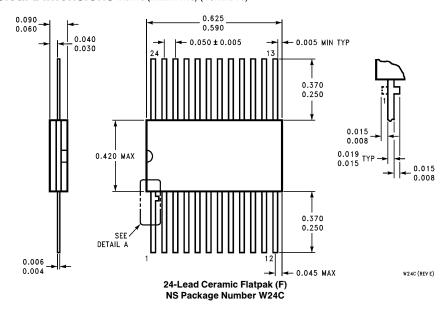








Physical Dimensions inches (millimeters) (Continued)



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